

Title (en)
ATMOSPHERIC PROCESS AND SYSTEM FOR CONTROLLED AND RAPID REMOVAL OF POLYMERS FROM HIGH DEPTH TO WIDTH ASPECT RATIO HOLES

Title (de)
VERFAHREN UND VORRICHTUNG UNTER ATMOSPHERISCHEN BEDINGUNGEN ZUM SCHNELLEN UND KOTROLIERTEN ENTFERNEN VON POLYMEREN AUS DURCH GROSSE TIEFEN-WEITEN-VERHÄLTNISSZAHLEN GEKENNZEICHNETEN LÖCHERN

Title (fr)
PROCEDE ET SYSTEME EN CONDITIONS ATMOSPHERIQUES POUR LE RETRAIT MAITRISE ET RAPIDE DE POLYMERES HORS DE TROUS A FACTEUR DE FORME PROFONDEUR/LARGEUR ELEVE

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Application
EP 00967233 A 20000928

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Abstract (en)
[origin: WO0123130A1] A hot arc-type plasma generating system is described to etch a polymer (44) on a substrate (10) used in the manufacture of semiconductor devices. The etching process is particularly useful to remove a polymer from high aspect ratio holes (40), that can include trenches, greater than about 10 to 1 and even greater than 50 to 1.

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